

MS2473 600 Watts, 50 Volts, Pulsed Avionics 1090 MHz

GENERAL DESCRIPTION The MS2473 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the 1090MHz frequency band. The device has gold thin-film metallization for proven highest MTTF. Low thermal resistance packaging reduces the junction temperature and extends device lifetime. ABSOLUTE MAXIMUM RATINGS			CASE OUTLINE M112
Maximu	m Power Dissipation @ 25°C ²	2300 Watts	
Maxim	Im Voltage and Current		
BVcbo	Collector to Base Voltage	65 Volts	
BVebo	Emitter to Base Voltage	3.5 Volts	
Ic	Collector Current	46 Amps	
	ım Temperatures		
	Temperature	$-65 \text{ to} + 150^{\circ}\text{C}$	
Operatin	g Junction Temperature	+ 200°C	.400 x .500 2LFL (M112)

ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg η _c RL _{IN}	Power Out Power Input = 150W Power Gain Collector Efficiency Input Return Loss	F = 1090 MHz Vcc = 50 Volts $PW = 10 \mu sec$ DF = 1% F = 1090 MHz	600 6.0 35 10	150		Watts Watts dB % dB

BVebo BVebo Ices h _{FE} Øjc²	Emitter to Base Breakdown Collector to Base Breakdown Collector to Emitter Leakage DC - Current Gain Thermal Resistance	Ie = 10 mA Ic = 25 mA Vce = 50V Vce = 5V, Ic = 1A	3.5 65 5	0.06	35 200	Volts Volts mA C/W	
---	---	--	----------------	------	-----------	-----------------------------	--

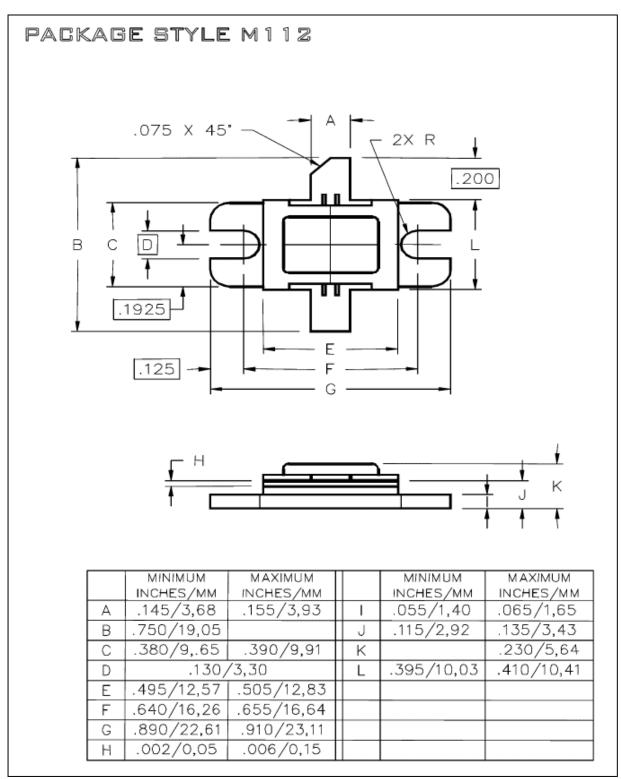
Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

Initial, January 2007

Microsemi – PPG reserves the right to change, without notice, the specifications and information contained herein. Visit our web site at <u>www.microsemi.com</u> or contact our factory direct.





Microsemi – PPG reserves the right to change, without notice, the specifications and information contained herein. Visit our web site at <u>www.microsemi.com</u> or contact our factory direct.